

Nobuyuki Matsuki

List of Publications by Year in descending order

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papers

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citations

1040056

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36
times ranked

330
citing authors

#	ARTICLE	IF	CITATIONS
1	Combinatorial screening of halide perovskite thin films and solar cells by mask-defined IR laser molecular beam epitaxy. <i>Science and Technology of Advanced Materials</i> , 2017, 18, 307-315.	6.1	26
2	Complete parameterization of the dielectric function of microcrystalline silicon fabricated by plasma-enhanced chemical vapor deposition. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	25
3	Concept and performance of a field-effect amorphous silicon solar cell. <i>Semiconductor Science and Technology</i> , 2004, 19, 61-64.	2.0	22
4	π-Conjugated polymer/GaN Schottky solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2011, 95, 284-287.	6.2	21
5	Investigation of local electrical properties of coincidence-site-lattice boundaries in location-controlled silicon islands using scanning capacitance microscopy. <i>Applied Physics Letters</i> , 2008, 93, 062102.	3.3	18
6	Photovoltaic Action in Polyaniline/n-GaN Schottky Diodes. <i>Applied Physics Express</i> , 2009, 2, 092201.	2.4	18
7	Ellipsometry Characterization of Hydrogenated Amorphous Silicon Layers Formed on Textured Crystalline Silicon Substrates. <i>Applied Physics Express</i> , 2010, 3, 116604.	2.4	11
8	Heteroepitaxial growth of gallium nitride on muscovite mica plates by pulsed laser deposition. <i>Solid State Communications</i> , 2005, 136, 338-341.	1.9	9
9	Anomalous capacitance-voltage characteristics of Pt-AlGaN/GaN Schottky diodes exposed to hydrogen. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1928-1930.	0.8	9
10	Nondestructive characterization of textured a-Si:H/c-Si heterojunction solar cell structures with nanometer-scale a-Si:H and In ₂ O ₃ :Sn layers by spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	9
11	Local network structure of a-SiC:H and its correlation with dielectric function. <i>Journal of Applied Physics</i> , 2013, 114, 233513.	2.5	8
12	Deep-Level Characterization of n-GaN Epitaxial Layers Using Transparent Conductive Polyaniline Schottky Contacts. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 01AD02.	1.5	7
13	Characterization of a-Si:H thin layers incorporated into textured a-Si:H/c-Si solar cell structures by spectroscopic ellipsometry using a tilt-angle optical configuration. <i>Thin Solid Films</i> , 2014, 569, 64-69.	1.8	7
14	Device simulation and fabrication of field effect solar cells. <i>Bulletin of Materials Science</i> , 1999, 22, 729-733.	1.7	6
15	Low-frequency capacitance-voltage study of hydrogen interaction with Pt-AlGaN/GaN Schottky barrier diodes. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009, 3, 266-268.	2.4	6
16	Photocapacitance spectroscopy study of deep-level defects in freestanding n-GaN substrates using transparent conductive polymer Schottky contacts. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011, 29, .	1.2	6
17	Impact of sputter-induced ion bombardment at the heterointerfaces of a-Si:H/c-Si solar cells with double-layered In ₂ O ₃ :Sn structures. <i>Japanese Journal of Applied Physics</i> , 2015, 54, 08KD09.	1.5	6
18	In-plane structure of an arsenic-adsorbed Si(001) surface probed with grazing-angle x-ray standing waves. <i>Physical Review B</i> , 1999, 60, 15546-15549.	3.2	5

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19	Improved performance of amorphous silicon thin film transistors by cyanide treatment. Applied Physics Letters, 2001, 78, 751-753.	3.3	5
20	Field-effect a-Si:H solar cells with transparent conductive oxide comb-shaped electrodes. Thin Solid Films, 2005, 486, 210-213.	1.8	5
21	Characteristics of AlN/Ni(111) Heterostructures and their Application to Epitaxial Growth of GaN. Japanese Journal of Applied Physics, 2006, 45, L396-L398.	1.5	5
22	HETEROINTERFACE PROPERTIES OF NOVEL HYBRID SOLAR CELLS CONSISTING OF TRANSPARENT CONDUCTIVE POLYMERS AND III-NITRIDE SEMICONDUCTOR. Journal of Nonlinear Optical Physics and Materials, 2010, 19, 703-711.	1.8	5
23	Electrical characterization of n-GaN epilayers using transparent polyaniline Schottky contacts. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2007-2009.	0.8	4
24	Transparent Conducting Polymer/Nitride Semiconductor Heterojunction Solar Cells. , 2011, , .		2
25	Deep-Level Characterization of n-GaN Epitaxial Layers Using Transparent Conductive Polyaniline Schottky Contacts. Japanese Journal of Applied Physics, 2011, 50, 01AD02.	1.5	2
26	Novel network control in hydrogenated amorphous silicon by molecular beam deposition method. Journal of Non-Crystalline Solids, 2004, 338-340, 382-385.	3.1	1
27	Direct observation of the electrical activity of coincidence site lattice boundaries in location-controlled silicon islands using scanning spread resistance microscopy. Journal of the Society for Information Display, 2009, 17, 293-297.	2.1	1
28	Unusual hydrogen distribution and its change in hydrogenated amorphous silicon prepared using bias electric-field molecular beam deposition. Applied Physics Letters, 2006, 89, 011909.	3.3	0
29	Deep-Level Characterization of Free-Standing HVPE-grown GaN Substrates Using Transparent Conductive Polyaniline Schottky Contacts. Materials Research Society Symposia Proceedings, 2011, 1309, 97.	0.1	0
30	Reply to 'Comment on 'Photovoltaic Action in Polyaniline/n-GaN Schottky Diodes'' Applied Physics Express, 2012, 5, 029102.	2.4	0
31	(Invited) A Novel Optical Characterization of a-Si:H/c-Si Interface Microstructures Based on Data of Positron Annihilation Spectroscopy. ECS Transactions, 2019, 92, 21-24.	0.5	0
32	Fabrication of Lead Halide Perovskite Thin Films by Laser Alternate Deposition: Variation of Physical Properties with Layered Structure. , 2021, , .		0
33	(Invited) A Novel Optical Characterization of a-Si:H/c-Si Interface Microstructures Based on Data of Positron Annihilation Spectroscopy. ECS Meeting Abstracts, 2019, , .	0.0	0
34	Inter-Layer Solid-Phase Reaction in Halide Perovskite Fabricated via Alternate Laser Deposition. , 2020, , .		0
35	Interlayer Solid-Phase Reaction in Halide Perovskite Thin Films Fabricated Via Alternate Infrared Laser Deposition. ECS Meeting Abstracts, 2020, MA2020-02, 1860-1860.	0.0	0
36	(Invited) Halide Perovskite Thin Films via Alternate Laser Deposition: Change in the Physical Properties with the Layered Structures. ECS Meeting Abstracts, 2021, MA2021-02, 637-637.	0.0	0